

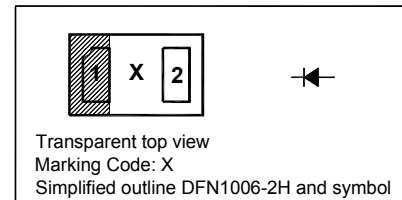
SDB720HP

SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for high speed switching circuit and small current
rectification applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Forward Current	I_O	200	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

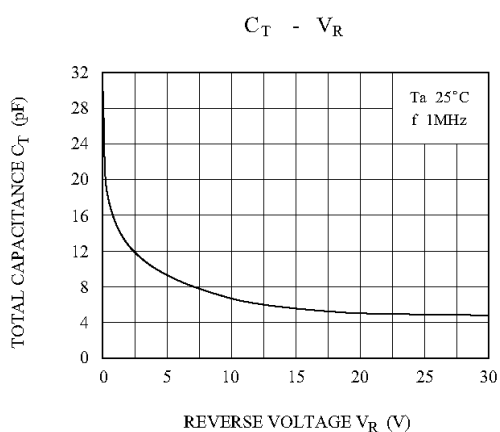
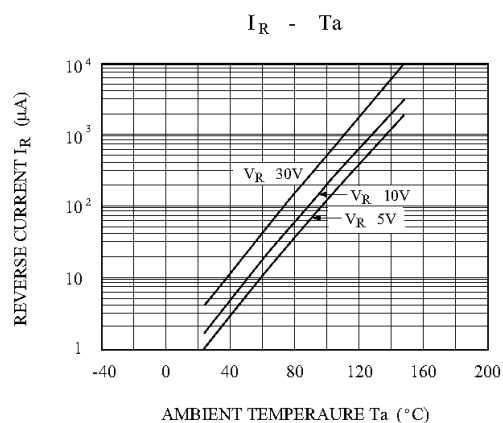
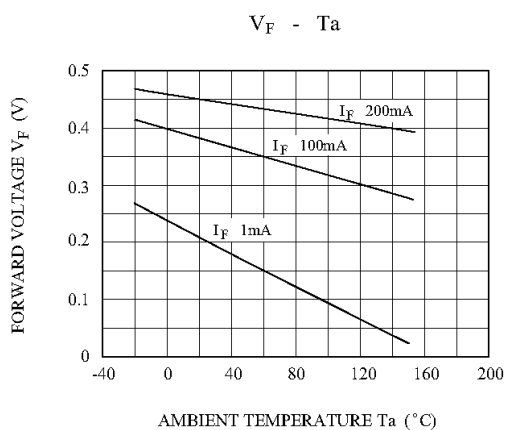
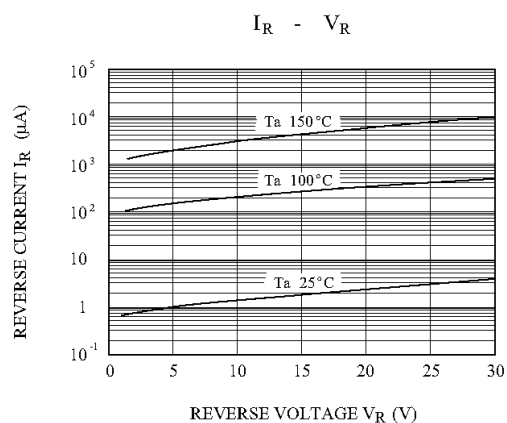
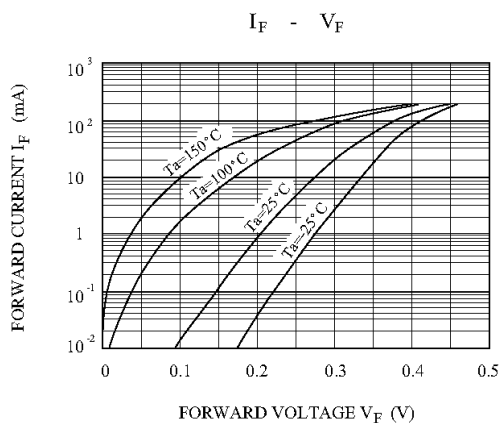
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	V_F	0.5	V
Reverse Current at $V_R = 10\text{ V}$	I_R	30	μA

TOP DYNAMIC



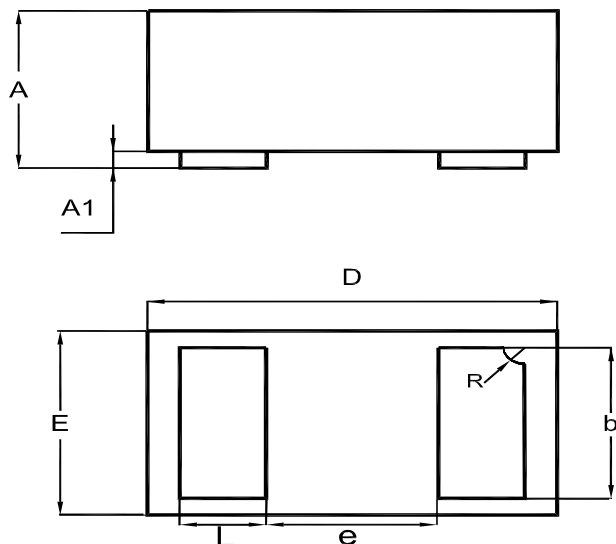
Dated: 19/05/2015 Rev: 02



PACKAGE OUTLINE

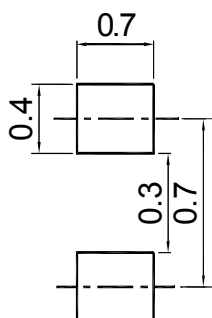
Plastic surface mounted package

DFN1006-2H



UNIT	A	A1	b	D	E	e	L	R
mm	0.51 0.46	0.05 0	0.55 0.45	1.05 0.95	0.65 0.55	0.4	0.3 0.2	0.15 0.05

Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
DFN1006-2H	8	4 ± 0.1	0.157 ± 0.004	178	7	5,000